ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention	STRUCTURE AND METHOD OF FORMING A BIPOLAR TRANSISTOR HAVING A VOID BETWEEN EMITTER AND EXTRINSIC BASE

Application Number :

Confirmation Number:

First Named Applicant: Rama Divakaruni

Attorney Docket Number: FIS920030414US1

Art Unit:

Examiner:

Search string: (5128271 or 5494836 or 5506427 or 5962880 or 6346453 or 20030057458 or 20030109109).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	5128271	1992-07-07	Bronner, et al.			
	2	5494836	1996-02-27	Imai			
	3	5506427	1996-04-09	Imai			
	4	5962880	1999-10-05	Oda, et al.			
	5	6346453	2002-02-12	Kovacic, et al.			

US Published Applications

Note: Applicant is not required to submit a paper copy of cited US Published Applications

init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
	1	20030057458	2003-03-27	Freeman, et al.			
	2	20030109109	2003-06-12	Freeman, et al.			

Signature

Examiner Name	Date
Fetsum Abah	8/24/04

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
FIS920030255US1	10/708,563
Applicant(s)	
Daniel C. Edelstein, et al.	
Filing Date	**Group Art Unit**
1/6/04	Not Yet Assigned

EXAMINER INITIAL		OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*
RA		Jagannathan, et al., "Self-aligned SiGe NPN Transistors with 285 GHz fMAX and 207 GHz fT in a Manufacturable Technology". IEEE Electron Device letters 23, 259 (2002)
		J.S. Rieh, et al., "SiGe HBTs with Cut-off Frequency of 350 GHz", International Electron Device Meeting Technical Digest, 771 (2002)
		M.W. Xu et al. "Ultra Low Power SiGe:C HBT for 0.18 um RF-FiCMOS, " Proceedings of the IEEE International Electron Devices Meeting, 2003.

EXAMINER	DATE CONSIDERED
Nelson Moseley	8/29/04

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.